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NTE2661 Silicon NPN Transistor Horizontal Deflection Output for HDTV TO3PBL Type Package

Features:

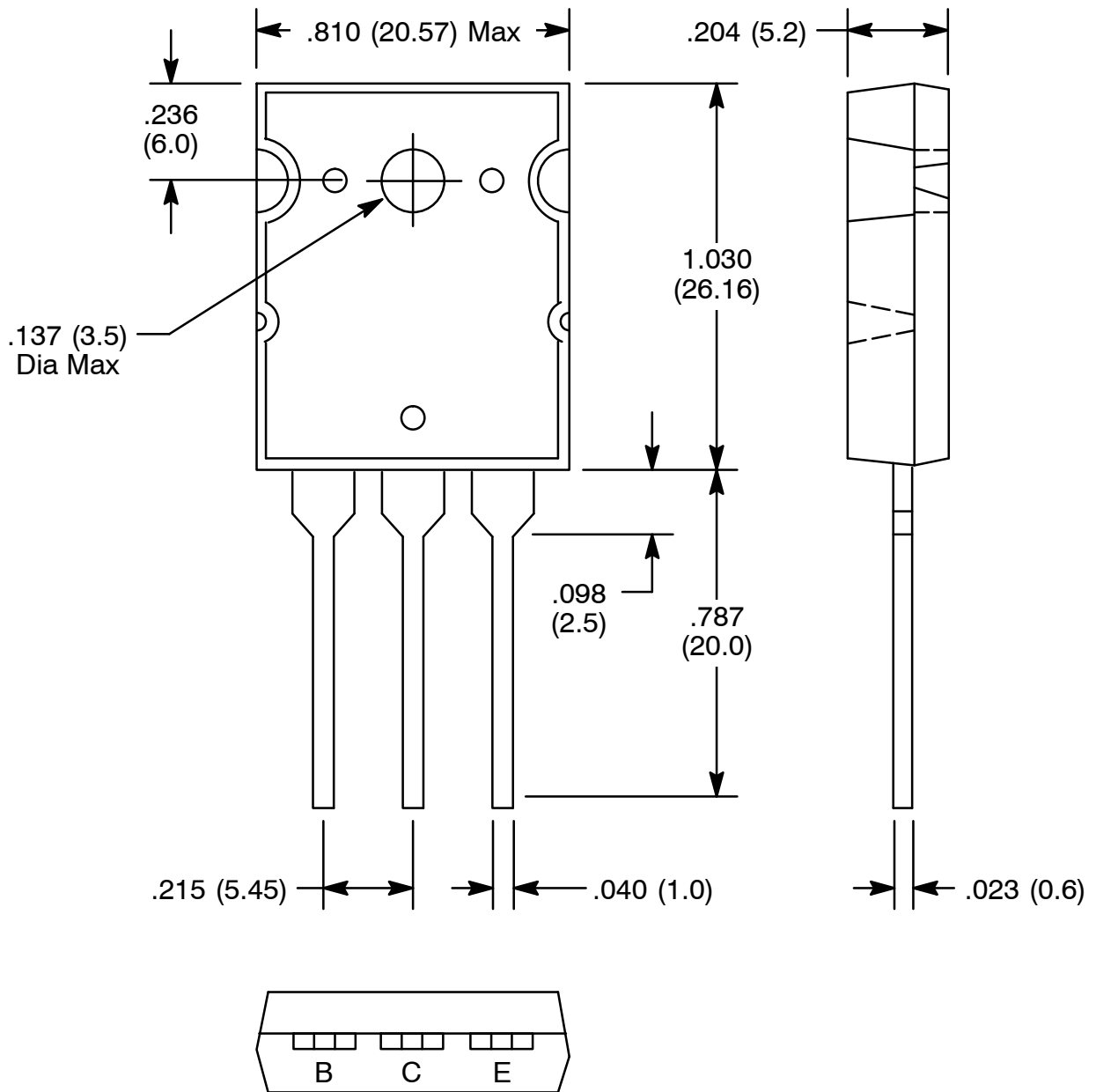
- High Speed: $t_f = 0.15 \text{ s Typ}$
- High Breakdown Voltage: $V_{CBO} = 1700V$
- Low Saturation Voltage: $V_{CE(sat)} = 3V \text{ Max}$

Absolute Maximum Ratings: ($T_A = +25^\circ C$ unless otherwise specified)

Collector-to-Base Voltage, V_{CBO}	1700V
Collector-to-Emitter Voltage, V_{CEO}	600V
Emitter-to-Base Voltage, V_{EBO}	5V
Collector Current, I_C	
Continuous	20A
Peak	40A
Base Current, I_B	10A
Collector Power Dissipation ($T_C = +25^\circ C$), P_C	200W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 1700V, I_E = 0$	-	-	1.0	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	-	-	10	A
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	600	-	-	V
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 2A$	10	-	30	-
		$V_{CE} = 5V, I_C = 11A$	4.5	-	8.5	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 11A, I_B = 2.75A$	-	-	3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 11A, I_B = 2.75A$	-	1.0	1.3	V
Transition Frequency	f_T	$V_{CE} = 10V, I_E = 0.1A$	-	1.7	-	MHz
Collector Output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	-	290	-	pF
Storage Time	t_{stg}	$I_C(\text{peak}) = 10A, I_{B1} = 1.8A, f_H = 64kHz$	-	2.5	4.0	s
Fall Time	t_f		-	0.15	0.3	s



NOTE: Pin2 connected to heatsink